

SK 35 NT

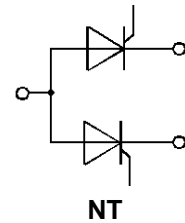
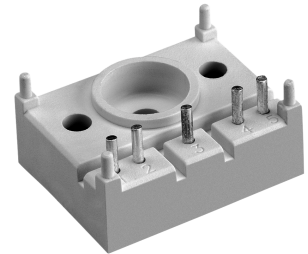
V_{RSM}	V_{RRM} V_{DRM}	I_{TAV} (maximum values for continuous operation) ($T_h = 85\text{ °C}$) 33 A
V	V	
900	800	SK 35 NT 08
1300	1200	SK 35 NT 12
1700	1600	SK 35 NT 16

SEMITOP® 1

Thyristor Module

SK 35 NT

Symbol	Conditions	Values	Units
I_{TAV}	$\sin 180^\circ$; $T_h = 100\text{ °C}$	23	A
	$T_h = 85\text{ °C}$	33	A
I_{TSM}	$T_{vj} = 25\text{ °C}$; 10 ms	1 000	A
	$T_{vj} = 125\text{ °C}$; 10 ms	900	A
i^2t	$T_{vj} = 25\text{ °C}$; 8,3...10 ms	5000	A ² s
	$T_{vj} = 125\text{ °C}$; 8,3...10 ms	4000	A ² s
t_{gd}	$T_{vj} = 25\text{ °C}$; $I_G = 1\text{ A}$; $di_G/dt = 1\text{ A}/\mu\text{s}$	1	μs
t_{gr}	$V_D = 0,67 V_{DRM}$	2	μs
$(dv/dt)_{cr}$	$T_{vj} = 125\text{ °C}$	1 000	V/ μs
$(di/dt)_{cr}$	$T_{vj} = 125\text{ °C}$; $f = 50\text{...}60\text{ Hz}$	50	A/ μs
t_q	$T_{vj} = 125\text{ °C}$; typ.	80	μs
I_H	$T_{vj} = 25\text{ °C}$; typ. / max	100 / 200	mA
I_L	$T_{vj} = 25\text{ °C}$; $R_G = 33\ \Omega$; typ. / max.	200 / 400	mA
V_T	$T_{vj} = 25\text{ °C}$; ($I_T = 120\text{ A}$); max.	1,8	V
$V_{T(TO)}$	$T_{vj} = 125\text{ °C}$	1	V
r_T	$T_{vj} = 125\text{ °C}$	6	m Ω
I_{DD} ; I_{RD}	$T_{vj} = 25\text{ °C}$ } $V_{DD} = V_{DRM}$	0,5	mA
	$T_{vj} = 125\text{ °C}$ } $V_{RD} = V_{RRM}$	15	mA
V_{GT}	$T_{vj} = 25\text{ °C}$; dc	2	V
I_{GT}	$T_{vj} = 25\text{ °C}$; dc	100	mA
V_{GD}	$T_{vj} = 125\text{ °C}$; dc	0,25	V
I_{GD}	$T_{vj} = 125\text{ °C}$; dc	5	mA
R_{thjh} ¹⁾	cont. per thyristor/per modul	0,8 / 0,4	K/W
	$\sin 180^\circ$ per thyristor/per modul	0,84 / 0,42	K/W
T_{vj}		- 40 ... + 125	$^\circ\text{C}$
T_{stg}		- 40 ... + 125	$^\circ\text{C}$
T_{solder}	terminals, 10 s	260	$^\circ\text{C}$
V_{isol}	a.c. 50 Hz; r.m.s. 1 s/1 min	3000 / 2500	V~
M_1	mounting torque	1,5	Nm
w		13	g
Case		T 9	



Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide (DCB)
- Glass passivated thyristor chips
- Up to 1600 V reverse voltage
- High surge currents
- UL recognized, file no. E 63 532

Typical Applications

- Soft starters
- Light control (studios, theaters)
- Temperature control

¹⁾ Thermal resistance junction to heatsink

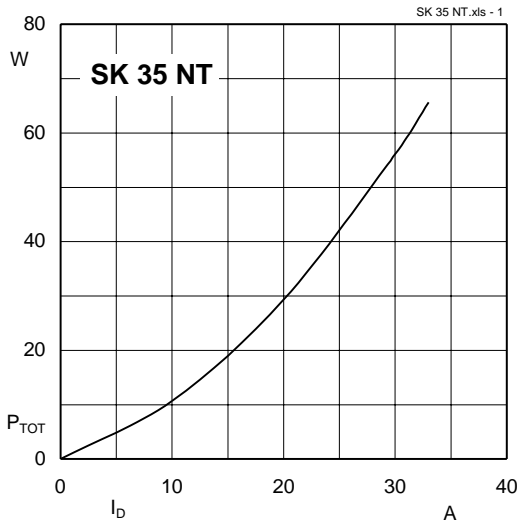


Fig. 1 Power dissipation vs. output current

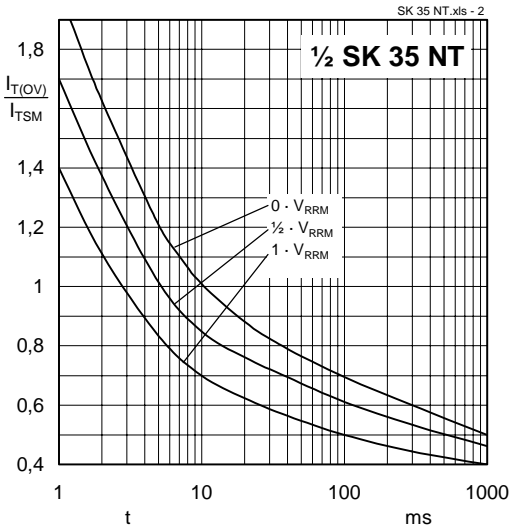


Fig. 2 Surge overload current vs. time

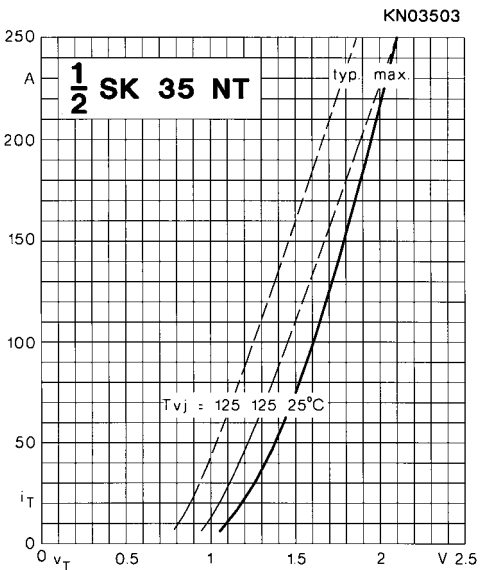


Fig. 3 Forward characteristic of single thyristor

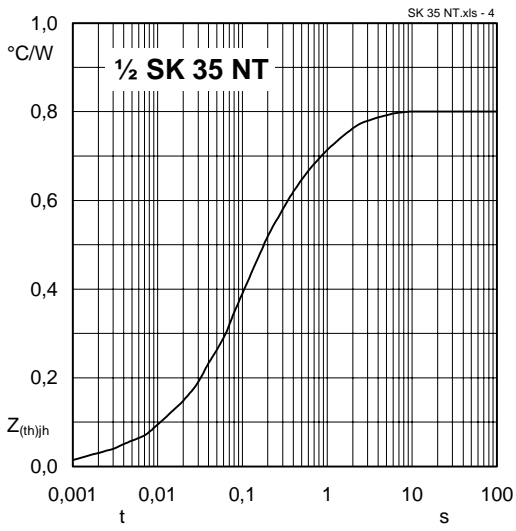


Fig. 4 Thermal transient impedance vs. time

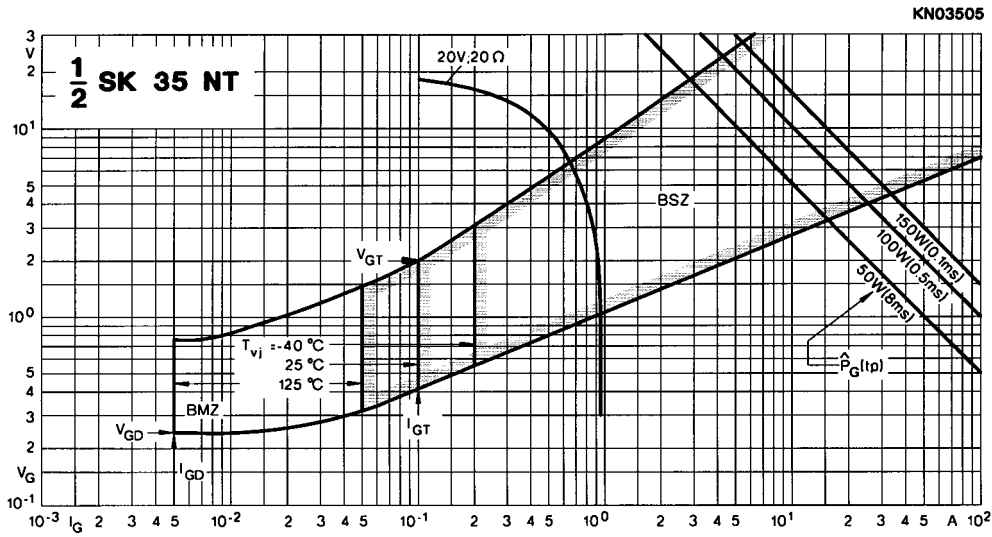
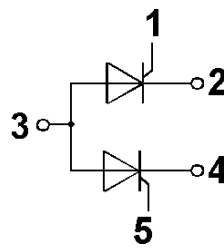
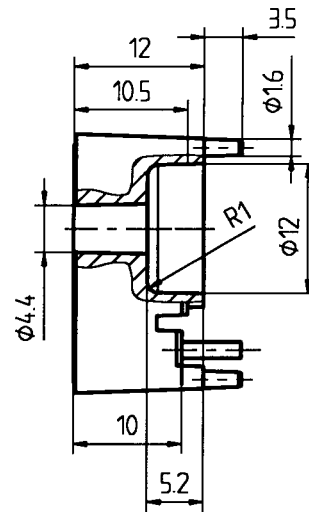
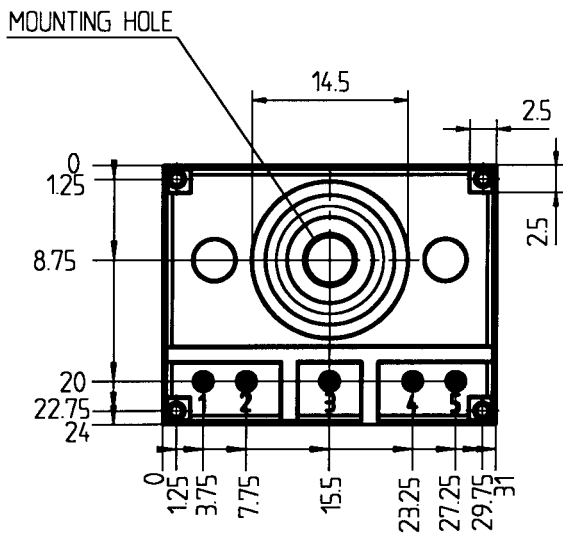
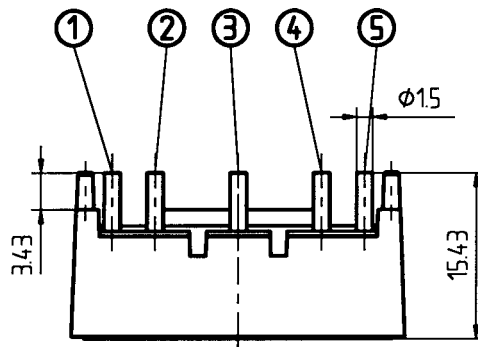


Fig. 5 Gate trigger characteristics

SEMITOP® 1
SK 35 NT

Case T 9



Dimensions in mm